

Form PTO 1649
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

241807US2DIV

SERIAL NO.

10/657,068

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Toshiaki IWAMATSU, et al.

FILING DATE

September 9, 2003

GROUP

2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Al	AA	5,466,960	11/14/1995	Vida ILDEREM, et al.	—	—	
Al	AB	5,079,182	01/07/1992	Vida ILDEREM, et al.	—	—	
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
Al	AO	10-0230610	11/15/1999	KOREA (with corr. US 5,466,960 and US 5,079,182)		X
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	
	AX	
	AY	
	AZ	

☐ Additional References sheet(s) attached

Examiner

Andy Murray

Date Considered

02/17/05

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241807US2DIV		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Toshiaki IWAMATSU et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>ah</i>	AA	6,261,882	07/2001	Kim	—	—	—
	AB	6,097,103	08/2000	Ishigaki	—	—	—
	AC	5,956,617	09/1999	Kimura et al.	—	—	—
	AD	5,612,243	03/1997	Verrett	—	—	—
	AE	5,294,822	03/1994	Verrett	—	—	—
	AF	5,223,456	06/1993	Malwah	—	—	—
	AG	4,786,611	11/1988	Pfister	—	—	—
	AH	4,476,482	10/1984	Scott et al.	—	—	—
	AI	4,374,700	02/1983	Scott et al.	—	—	—
	AJ						
AK							
AL							
AM							
AN							
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO			
<i>ah</i> <i>ah</i> <i>ah</i>	AO	2-159035	06/19/90	JAPAN (w/ English Extract)			X
	AP	9-275134	10/21/97	JAPAN (w/ English Extract)			X
	AQ	6-204334	07/22/94	JAPAN (w/ English Extract)			X
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>ah</i> <i>ah</i> <i>ah</i>	AW	M. INOHARA, et al., "Copper Contamination Induced Degradation of MOSFET Characteristics and Reliability", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 26-27					
	AX	Kazuyuki HOZAWA, et al., "Copper distribution behavior near a SiO ₂ /Si interface by low-temperature (<400°C) annealing and its influence on electrical characteristics of MOS-capacitors", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 24-25					
	AY	A. STEEGEN, et al., "Silicide and Shallow Trench Isolation line width dependent stress induced junction leakage", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 180-181					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <i>Andy Murray</i>				Date Considered 10/16/04			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							